
Symposium (Oral) | Symposium (technical) | Applications of new ferroelectric materials for the future electric devices

[20p-C309-1~10]Applications of new ferroelectric materials for the future electric devices

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△ : Presentation by Applicant for JSAP Young Scientists Presentation Award

▲ : English Presentation

▼ : Both of Above

No Mark : None of Above

4:30 PM - 5:00 PM

[20p-C309-8]Status and prospects of ferroelectric HfO₂ tunnel junction

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Keywords:non-volatile memory, ferroelectric, ferroelectric tunnel junction